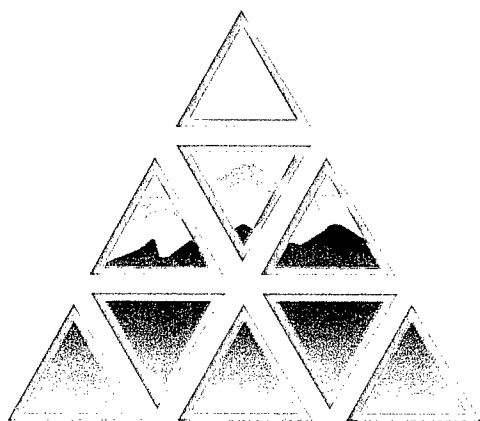


**8th International Conference on
II-VI Compounds**

*25-29 Aug 97
Grenoble, France*



**GRENoble
II-VI '97**

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ADVANCE PROGRAMME

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FOREWORD

The 8th *International Conference on II-VI Compounds* will be held in Grenoble, 25-29 August 1997. This is a continuation of the series of meetings held in Durham (1982), Aussois (1985), Monterey (1987), Berlin (1989), Tamano (1991), Newport (1993) and Edinburgh (1995). It is organised in partnership by the three laboratories in Grenoble involved in II-VI semiconductors research: the CEA / DRFMC, the CNRS / Université J. Fourier, and the CEA / LETI.

SCOPE AND TOPICS

The conference will focus on fundamental aspects and on recent perspectives for applications of narrow and wide bandgap II-VI semiconductors. Areas of interest include: materials science, where many long-standing problems (particularly compensation) are still to be solved, low-dimensional physics including semi-magnetic heterostructures, and optoelectronic applications. The following main topics will be covered:

- materials growth : narrow and wide bandgap materials, substrates for devices, control of doping, epitaxial growth
- fundamental properties and characterisation : theory, electronic properties, surfaces, interfaces, defects, transport, electroluminescence, non-linear optics, photorefractive effects
- low-dimensional systems : quantum wells, wires and boxes, superlattices, nanocrystals
- optoelectronic devices : IR detectors, blue lasers, X- and γ -ray detectors and other applications.

Other emerging subjects such as microcavities will also be highlighted.

SPECIAL SESSION

A special session on *Wide Bandgap Lasers* is scheduled for the Tuesday evening, 26 August 1997. It will be organised by Prof. Arto Nurmikko, Brown University, USA and Dr. Akira Ishibashi, Sony Corporation, Japan.



CO - CHAIRMEN

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Exhibition

Alain Million

*Announcements and
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Dr. Le Si Dang

II - VI Conference Secretariat

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D.J.	Olego	<i>Philips Lab., Briarcliff Mr, USA</i>
H.F.	Schaake	<i>Texas Instruments, Dallas, USA</i>
R.	Triboulet	<i>CNRS, Meudon, France</i>
T.	Yao	<i>Univ. Tohoku, Japan</i>
A.	Yoshikawa	<i>Univ. Chiba, Japan</i>



CONFERENCE VENUE

The meeting will be held at the Atria Conference Centre in the centre of Grenoble. Atria has excellent facilities and the Novotel Hotel occupies part of the building. Conference lunches, included in the conference fee, will be provided in the Atria centre to enhance opportunities for scientific exchange among the participants.

CITY OF GRENOBLE

The city of Grenoble, capital of the *Dauphiné*, is located in a broad valley surrounded by high mountains of the Alpine chain. Site of the 1968 Winter Olympic Games, it is a famous centre for mountain excursions, climbing and hiking.

Grenoble, born as a Roman city, has made its mark on French history. The Revolution began here with the events of 1788, one year before Paris. The musician Hector Berlioz was a son of the *Dauphiné*, Stendhal gave Grenoble its literary reputation, Champollion added to its reputation by deciphering the Egyptian hieroglyphics, and Joseph Fourier, the famous physicist and mathematician, was an illustrious Prefect of the city.

The traditional activities such as paper mills and glove making have given way to hydroelectric energy production and scientific research. The *Rhône-Alpes* region has become the centre of highly competitive computer and chemical industries.

Grenoble has always been famous for its universities, drawing students from all over the world. Its student population now exceeds 40 000, while its research laboratories include 8 500 research scientists in physics, mathematics, computer science, biology and medicine. Major research institutes include the CEA atomic energy research centre, the CNRS Louis Néel laboratories, the Laue-Langevin neutron diffraction laboratory, the European Synchrotron Research Facility and the Grenoble High Magnetic Field Laboratory.

The usual maximum daytime temperatures for late August are between 25 and 30° C (77 - 86° F).

LABORATORY VISIT

A visit of the European Synchrotron Radiation Facility will be organised on Friday afternoon, 29 August 1997.



SOCIAL PROGRAMME

Sunday Afternoon

24 August

An excursion is organised on Sunday afternoon for persons arriving early. The departure will be at 12:30 p.m. in front of the Conference centre. Participants will be taken by coach (~1.5hrs) to the site of *La Meije* (3990 m) one of the most majestic mountains near Grenoble. A panoramic cable car lift travels to ~3200 m, but also sets down at ~2400 m. Participants will be free to enjoy the panorama offered by the surroundings mountains. Advance booking is required.

Sunday Evening

24 August

A reception with buffet, starting at 7 p.m., will be held at the Atria Conference Centre throughout Sunday evening to allow delegates and accompanying persons flexibility in their arrival times.

Monday Evening

25 August

The town Council and the Mayor of the City of Grenoble are kindly providing a reception to the conference attendees and accompanying persons. The reception will be held in the Grenoble Art Gallery, which will be opened for free visit afterwards.

Wednesday Afternoon / Evening

27 August

There will be no technical session on the Wednesday afternoon, and an excursion is programmed. Please note that the scientific sessions will start at 8:30 a.m. on Wednesday to allow the excursion to begin at 1.15 p.m. Coaches will take participants to the beautiful old city of *Annecy* in Savoy, which offers very pleasant walks along its narrow passages and canal sides. A boat tour on the Lake of Annecy is programmed.

Thursday Evening

28 August

The conference banquet will be held in the *Château du Touvet*, a 15th Century castle 30 km from Grenoble. The castle has beautiful fountains and large gardens which will be opened to participants before the dinner. Advance booking is required.

ACCOMPANYING PERSONS

The city of Grenoble and its surroundings are full of places where both art and nature can be admired. A number of activities will be arranged on a daily basis by the conference Local Committee.



CALENDAR OF EVENTS

All sessions will be held in the Atria Conference Centre unless otherwise indicated.

Sunday, 24 August 1997

12:00	a.m.	-	9:00	p.m.	Registration
12:30	p.m.				Excursion to La Meije
7:00	p.m.	-	10:00	p.m.	Buffet Reception

Monday, 25 August 1997

8:00	a.m.	-	6:00	p.m.	Registration and Speakers' Check-in
8:45	a.m.	-	9:00	a.m.	Opening Session
9:00	a.m.	-	10:30	a.m.	Lasers I
10:30	a.m.	-	11:00	a.m.	Coffee Break
11:00	a.m.	-	12:30	p.m.	Doping I
12:30	p.m.	-	2:00	p.m.	Lunch
2:00	p.m.	-	3:30	p.m.	Heterostructures I
3:30	p.m.	-	4:00	p.m.	Coffee Break
4:00	p.m.	-	5:30	p.m.	Nanostructures I
7:00	p.m.				City Reception

Tuesday, 26 August 1997

8:00	a.m.	-	6:00	p.m.	Registration and Speakers' Check-in
9:00	a.m.	-	10:30	a.m.	Lasers II
10:30	a.m.	-	11:00	a.m.	Coffee Break
11:00	a.m.	-	12:30	p.m.	Nonlinear Optics
12:30	p.m.	-	2:00	p.m.	Lunch
2:00	p.m.	-	3:30	p.m.	Detectors
3:30	p.m.	-	6:00	p.m.	Posters I (Refreshments available)
8:00	p.m.	-	10:00	p.m.	Special Session: Wide Bandgap Lasers

Wednesday, 27 August 1997

8:00	a.m.	-	12:00	a.m.	Registration and Speakers' Check-in
8:30	a.m.	-	10:00	a.m.	Diluted Magnetic Semiconductors I
10:00	a.m.	-	10:30	a.m.	Coffee Break
10:30	a.m.	-	12:00	a.m.	Heterostructures II
12:00	a.m.	-	1:00	p.m.	Lunch
1:15	p.m.				Excursion to Annecy

Thursday, 28 August 1997

8:00	a.m.	-	6:00	p.m.	Registration and Speakers' Check-in
9:00	a.m.	-	10:30	a.m.	Parallel Session: Materials
9:00	a.m.	-	10:30	a.m.	Parallel Session: Diluted Magnetic Semiconductors II (*)
10:30	a.m.	-	11:00	a.m.	Coffee Break
11:00	a.m.	-	12:30	p.m.	Parallel Session: Heterostructures III
11:00	a.m.	-	12:30	p.m.	Parallel Session: Doping II (*)



12:30	p.m.	-	2:00	p.m.	Lunch
2:00	p.m.	-	3:45	p.m.	Parallel Session: Microcavities
2:00	p.m.	-	3:45	p.m.	Parallel Session: Narrow Gap Semiconductors (*)
3:45	p.m.	-	6:00	p.m.	Poster II (Including post-deadline papers; Refreshments available)
6:30	p.m.				Conference Banquet

Friday, 29 August 1997

8:00	a.m.	-	1:00	p.m.	Registration and Speakers' Check-in
9:00	a.m.	-	10:30	a.m.	Surfaces and Interfaces
10:30	a.m.	-	11:00	a.m.	Coffee Break
11:00	a.m.	-	12:30	a.m.	Nanostructures II
12:30	p.m.	-	12:45	p.m.	Closing Session
12:45	p.m.	-	2:00	p.m.	Lunch
2:00	p.m.				Visit of the European Synchrotron Radiation Facility

(*) These sessions will be held in the *Ecole Supérieure de Commerce* (ESC) amphitheatre.



POST-DEADLINE PAPERS

A limited number of post-deadline papers describing new results of particular significance, obtained after the March deadline, will be accepted at the discretion of the Programme Committee. Abstracts must be received by 1 August 1997. Abstracts received after the deadline will not be considered. A letter describing the significance of the contribution must be sent with the abstract.

For writing your abstract, please conform to the directions for abstracts contained in the Second Circular or on the Conference Website:

http://spectro.ujf-grenoble.fr/~icc_2_6

A copy of the abstract of accepted post-deadline papers will be distributed to the participants during the conference.

ORAL PRESENTATIONS

The time assigned for oral presentation of contributed papers is 15 minutes (12' for presentation and 3' for discussion). The invited speakers' assigned time is 30 minutes (25' for presentation and 5' for discussion).

POSTER SESSION

Each author will be provided with a 1.5 m high x 0.9 m wide bulletin board on which to display a summary of the paper. Material needed for fixing the summaries on the bulletin boards will be available on site.

Authors should remain in the vicinity of their poster for the whole duration of the session (~2hrs).

REGISTRATION

The conference Registration Desk will be opened from 12:00 a.m. to 9:00 p.m. on Sunday 24 August and from 8:00 a.m. to 6:00 p.m. on the following meeting days (except Wednesday, 8:00 a.m. - 12:00 a.m.).



SPEAKERS CHECK-IN

All speakers are requested to check in at the Registration Desk before the beginning of the sessions. Authors who have 35-mm slides are requested also to preload and preview their slides at the Registration Desk at least 30 minutes before their session begins. Slides may be retrieved at the same location after the session. Universal trays will be available for each author.

AUDIOVISUAL EQUIPMENT

In the meeting rooms there will be the following equipment available: microphone, pointer, overhead projector, video projection equipment, 50 mm x 50 mm (35-mm) slide projector. Additional equipment may be available on request. Please contact the Conference Secretariat by 1st August 1997 if you have special audiovisual requirements.

PUBLICATION

The proceedings will be published in a fully refereed special issue of the *Journal of Crystal Growth*. Papers must be presented at the Conference by one of the co-authors to be considered for publication.

MESSAGES AND ON-SITE SERVICES

During the meeting the following facilities will be available for receiving messages:

Fax +33 - (0)476 708 462

Tel. +33 - (0)476 708 445

A limited email service will be provided. Urgent outgoing messages will be sent by the conference staff. Participants can be reached by writing to the following address:

II_VI_97@cea.fr

with the participant's name as subject line. These incoming messages will be printed out and delivered to the recipient.

A photocopying machine will be available to enable participants to make extra copies of their papers if needed.

II-VI '97

AUTHOR INDEX

12.00 a.m.

- Mo-07 Spin flip Raman spectroscopy of nitrogen acceptors in ZnSe layers with different biaxial strains**, C. Orange, W. Heimbrodt, D. Wolverson, and J.J. Davies, Univ. East Anglia, Norwich, UK

12.15 a.m.

- Mo-08 The phosphorous acceptor in ZnSe**, G. Neu, C. Morhain, E. Tournié, and J.-P. Faurie, CRHEA-CNRS, Sophia Antipolis, Valbonne, France

12.30 p.m. - 2.00 p.m. - Lunch

HETEROSTRUCTURES I

(2.00 p.m. - 3.30 p.m.)

2.00 p.m. (invited)

- Mo-09 Dark exciton states and magneto-excitons in wide-gap II-VI quantum wells**, J. Puls, F. Henneberger, and M. Rabe, Humboldt-Univ. Berlin, Berlin, Germany

2.30 p.m.

- Mo-10 Optical study of a tunable-density two-dimensional electron gas in a CdTe/CdZnMgTe single quantum well**, S. Lovisa, R.T. Cox, K. Saminadayar, and N. Magnea, CEA-Grenoble, France

2.45 p.m.

- Mo-11 High mobility 2D electron gas in iodine modulation doped CdTe/CdMgTe heterostructures**, G. Karczewski, J. Jaroszynski, A. Barcz, T. Wojtowicz, and J. Kossut, Pol. Acad. Sci., Warsaw, Poland

3.00 p.m.

- Mo-12 Resonant tunneling in II-VI wide-gap heterostructures**, M. Keim, U. Lunz, F. Fischer, G. Reuscher, A. Waag, T. Kümmell, A. Forchel, and G. Landwehr, Univ. Würzburg, Würzburg, Germany

3.15 p.m.

- Mo-13 Electron and hole g factor anisotropy in CdTe/CdMgTe quantum wells**, A.A. Kiselev, E.L. Ivchenko, A.A. Sirenko, T. Ruf, M. Cardona, D.R. Yakovlev, W. Ossau, A. Waag, and G. Landwehr, A.F. Ioffe Phys.-Tech. Inst., St. Petersburg, Russia, MPI, Stuttgart, Germany, Univ. Würzburg, Würzburg, Germany

3.30 p.m. - 4.00 p.m. Coffee Break

NANOSTRUCTURES I

(4.00 p.m. - 5.30 p.m.)

4.00 p.m. (invited)

- Mo-14 Self organized growth, ripening and optical studies of wide-bandgap II-VI quantum dots**, J.L. Merz, S. Lee, and J.K. Furdyna, Univ. Notre Dame, Indiana, USA

4.30 p.m.

Mo-15 Spontaneous formation of II-VI dot arrays and wires, Baoping Zhang, Wenxin Wang, Takashi Yasuda, and Yusaburo Segawa, Inst. Phys. and Chem. Res. (RIKEN), Sendai, Japan

4.45 p.m.

Mo-16 Self-Organized CdSe/ZnSe quantum dots on a ZnSe (111)A surface, E. Kurtz, H.D. Jung, K.T. Park, T. Hanada, Z. Zhu, T. Sekiguchi, and T. Yao, Tohoku Univ., Sendai, Japan

5.00 p.m.

Mo-17 Self-assembled (Zn,Cd)Se quantum dots, M. Lowisch, M. Rabe, F. Kreller, and F. Henneberger, Humboldt Univ. Berlin, Berlin, Germany

5.15 p.m.

Mo-18 Atomic layer epitaxy of CdTe/MnTe tilted and serpentine superlattices, J.M. Hartmann, F. Kany, M. Charleux, F. Chautain, J.L. Rouvière, and H. Mariette, CEA-CNRS, Univ. J. Fourier, Grenoble, France

TUESDAY

LASERS II

(9.00 a.m. - 10.30 a.m.)

9.00 a.m.

- Tu-01 Room-temperature CW operation of II-VI laser grown on ZnSe substrate cleaned with hydrogen plasma**, T. Ohno, A. Ohki, and T. Matsuoka, NTT Opto-electronics Lab., Kanagawa, Japan

9.15 a.m.

- Tu-02 Fabrication of ZnSe-based laser diode structure by photoassisted MOVPE**, K. Ogata, D. Kawaguchi, N. Nishiyama, Sz. Fujita, and Sg. Fujita, Univ. Kyoto, Kyoto, Japan

9.30 a.m.

- Tu-03 RT lasing and efficient optical confinement in CdSe/ZnMgSSe submonolayer superlattice**, I. Krestnikov, S. Ivanov, M. Maximov, S. Sorokin, P. Kop'ev, N. Ledentsov, A. Hoffmann, and D. Bimberg, A.F. Ioffe Phys.-Tech. Inst., St. Petersburg, Russia, Tech. Univ. Berlin, Berlin, Germany

9.45 a.m.

- Tu-04 On the laser action of ZnCdSe multiple-quantum well structures: Bi-excitons at elevated temperatures**, F. Kreller, J. Puls, H.-J. Wünsche, and F. Henneberger, Humboldt-Univ. Berlin, Berlin, Germany

10.00 a.m.

- Tu-05 Thermal and electrostatic stability of biexcitons in ZnCdSe/ZnSe quantum wells**, L. Calcagnile, M. Lomascolo, G. Coli, R. Cingolani, L. Sorba, and A. Franciosi, INFN, Univ. Lecce, Lecce, Italy, TASC-INFN, Trieste, Italy

10.15 a.m.

- Tu-06 Room-temperature ultraviolet lasing and optical gain of ZnO hexagonal microcrystallites**, Z.K. Tang, P. Yu, George K.L. Wong, M. Kawasaki, A. Ohtomo, H. Koinuma, and Y. Segawa, Hong Kong Univ. of Sci. and Tech., Hong Kong, Tokyo Inst. Tech., Yokohama, Japan

10.30 a.m. -- 11.00 a.m. Coffee Break

NON LINEAR OPTICS

(11.00 a.m. - 12.30 p.m.)

11.00 a.m. (invited)

- Tu-07 Coherent exciton-biexciton interaction studied by femtosecond spectroscopy**, I. Galbraith, Univ. Heriot-Watt, Edinburgh, UK

11.30 a.m. (invited)

Tu-08 Excitonic optical nonlinearities and dynamics in II-VI heterostructures and laser diodes, J. Gutowski, U. Neukirch, and P. Michler, Univ. Bremen, Bremen, Germany

12.00 a.m.

Tu-09 Two-photon absorption of biexcitons in ZnS-based quantum wells, K. Yoshimura, H. Watanabe, Y. Yamada, T. Taguchi, F. Sasaki, S. Kobayashi, and T. Tani, Yamaguchi Univ., Yamaguchi, Japan, ETL, Tsukuba, Japan

12.15 a.m.

Tu-10 A spectroscopic study into the piezoelectric effect in ZnSe/ZnCdSe quantum wells grown on (211)B GaAs, J.S. Milnes, C. Morhain, S.A. Telfer, W. Meredith, T.A. Steele, K.A. Prior, B.C. Cavenett, Heriot-Watt Univ., Edinburgh, UK

12.30 p.m. - 2.00 p.m. Lunch

DETECTORS

(2.00 p.m. - 3.30 p.m.)

2.00 p.m. (invited)

Tu-11 Progress in HgCdTe homojunction infrared detectors, J.P. Chatard, and P. Tribolet, SOFRADIR, Chatenay-Malabry, France

2.30 p.m. (invited)

Tu-12 HgCdTe heterojunctions for infrared multispectral sensor applications, S.M. Johnson, SBRC, Santa Barbara, California, USA

3.00 p.m.

Tu-13 MBE-grown HgCdTe SAM structures for high speed and low noise 1.3-1.6 μ m avalanche photodetectors, O.K. Wu, R.D. Rajavel, T.J. DeLyon, J.E. Jensen, M.D. Jack, K. Kosai, G.R. Chapman, S. Sen, B.A. Baumgratz, B. Walker and B. Johnson, Hugues Research Laboratories, Malibu, California, USA, Santa Barbara Research Center, Goleta, California, USA, University of Maryland, Maryland, USA

3.15 p.m.

Tu-14 Advances in CdHgTe N-P-N photoconductive structures, M.A. Le Meur, M. Cuniot, J.F. Rommeluère, A. Tromson-Carli, R. Triboulet, and Y. Marfaing, CNRS, Bellevue, Meudon, France

3.30 p.m. - 6.00 p.m. POSTER SESSION I

8.00 p.m. Special Session: WIDE BANDGAP LASERS

WEDNESDAY

DILUTED MAGNETIC SEMICONDUCTORS I

(8.30 a.m. - 10.00 a.m.)

8.30 a.m. (invited)

We-01 Confinement effects in semimagnetic semiconductors, Tomazs Dietl, Acad. of Sci., Warsaw, Poland

9.00 a.m.

We-02 Ferromagnetic transition induced by a two-dimensional hole gas in a semimagnetic quantum well, J. Cibert, A. Haury, A. Wasiela, Y. Merle d'Aubigné, T. Dietl, A. Arnoult, and S. Tatarenko, Univ. J. Fourier, Grenoble, France

9.15 a.m.

We-03 The bifurcation of exciton free-magnetic polarons in CdMnTe-CdTe-CdMgTe asymmetric single quantum wells, S. Takeyama, Y.G. Semenov, T. Karasawa, G. Karczewski, T. Wojtowicz, and J. Kossut, Himeji Inst. of Techn., Hyogo, Japan, Univ. Tokyo, Tokyo, Japan, Acad. Sci. Ukraine, Kiev, Ukraine, Osaka City Univ. Osaka, Japan, Polish Acad. of Sci., Warsaw, Poland

9.30 a.m.

We-04 Magnetic polaron associated with hole in zinc-blende semimagnetic semiconductors, A.K. Bhattacharjee and C. Benoit à la Guillaume, Univ. Paris Sud, Orsay, France, Univ. Paris VI et VII, Paris, France

9.45 a.m.

We-05 Exciton dynamics in diluted-magnetic II-VI semiconductor nanostructures, Yasuo Oka, Kohei Yanata, Shuji Takano, and Hiroshi Okamoto, Tohoku Univ., Sendai, Japan, CREST, JST, Saitama, Japan

10.00 a.m. - 10.30 a.m. Coffee Break

HETEROSTRUCTURES II

(10.30 a.m. - 12.00 a.m.)

10.30 a.m.

We-06 Hetero-epitaxial growth of Be-chalcogenides based semiconducting alloys on Si substrates, J.-P. Faurie, P. Brunet, V. Bousquet, and E. Tournié, CRHEA-CNRS, Sophia Antipolis, Valbonne, France

10.45 a.m.

- We-07 Structural properties of homoepitaxial and heteroepitaxial ZnSe based laser structures**, H. Heinke, V. Grossmann, M. Behringer, H. Wenisch, and D. Hommel, Univ. Bremen, Bremen, Germany

11.00 a.m.

- We-08 Lattice-matched ZnCdSe/InGaAs (001) heterostructures and blue-green lasers**, B.H. Müller, R. Lantier, L. Sorba, S. Rubini, M. Lazzarino, S. Heun, A. Franciosi, F. Romanato, A. Drigo, J.-M. Bonard, J.D. Ganiere, L. Lazzarini, and G. Salviati, TASC-INFM, Trieste, Italy, Univ. Padova, Padova, Italy, EPFL, Lausanne, Switzerland, MASPEC-CNR, Parma, Italy

11.15 a.m.

- We-09 Observation of different growth modes in the MOVPE of CdS/ZnS and CdSe/ZnSe by in-situ reflectance anisotropy spectroscopy**, C. Meyne, U.W. Pohl, J.-T. Zettler, and W. Richter, TU-Berlin, Berlin, Germany

11.30 a.m.

- We-10 ZnSe/ZnMgSSe QW structures grown by MOVPE on ZnSe (100), ZnSe (511) and GaAs (100) substrates**, V.I. Kozlovsky, A.B. Krysa, Yu. V. Korostelin, P.V. Shapkin, H. Kalisch, M. Luenenbuerger, and M. Heuken, Inst.of RAS, Moscow, Russia, RWTH Aachen, Aachen, Germany

11.45 a.m.

- We-11 Investigation of the surfactant effect of Sn in ZnSe by RDS and RHEED**, H.D. Jung, N. Kumagai, T. Hanada, E. Kurtz, Z. Zhu, T. Yasuda, H.S. Park, T.I. Kim, and T. Yao, Tohoku Univ., Sendai, Japan, Joint Res. Center Atom Tech., Tsukuba, Japan, Samsung Adv. Inst. Tech., Suwon, Korea

12.00 a.m. - 1.15 p.m. Lunch

THURSDAY

MATERIALS

(9.00 a.m. - 10.30 a.m.)

Session A - Auditorium ATRIA Centre

9.00 a.m. (invited)

Th-a01 CdTe and CdZnTe materials for room temperature X-ray and gamma-ray detectors, Y. Eisen, and A. Shor, SOREQ NRC, Yavne, Israel

9.30 a.m.

Th-a02 Vapour growth of CdTe single crystals in a semi-closed arrangement, M. Laasch, T. Kunz, J. Meinhardt, and K.W. Benz, Univ. Freiburg, Freiburg, Germany

9.45 a.m.

Th-a03 Seeded vapour phase free growth of ZnSe single crystals in the <111> direction, Yu.V. Korostelin, V.I. Kozlovsky, S.H. Lee, A.S. Nasibov, S.S. Park, and P.V. Shapkin, Lebedev Phys. Inst., RAS, Moscow, Russia, Samsung Adv. Inst.Tech., Suwon, Korea

10.00 a.m.

Th-a04 Photoluminescence quantum efficiency of various ternary II-VI semiconductor solid solutions, R. Westphäling, S. Bauer, and C. Klingshirn, Univ. Karlsruhe, Karlsruhe, Germany

10.15 a.m.

Th-a05 Magneto-excitons and Landau levels in strained ZnSe and ZnTe layers, S. Lee, F. Michl, M. Dobrowolska, J.K. Furdyna, U. Roessler, Univ. Notre Dame, Notre Dame, USA, Univ. Regensburg, Regensburg, Germany

DILUTED MAGNETIC SEMICONDUCTORS II

(9.00 a.m. - 10.30 p.m.)

Session B- Amphitheatre ESC

9.00 a.m.

Th-b01 Excitons In CdMnTe quantum wells with parabolic confining potential, T. Wojtowicz, M. Kutrowski, G. Cywinski, G. Karczewski, E. Janik, E. Dynowska, and J. Kossut, Polish Acad. Sci., Warsaw, Poland

9.15 a.m.

Th-b02 Confined magnons in layered MnTe/CdTe structures, M. Jouanne, W. Szuszkiewicz, J.F. Morhange, M.A. Kanehisa, J.M. Hartmann, H. Mariette, E. Dynowska, G. Karczewski, T. Wojtowicz, J. Kossut, and J. Barnas, Univ. Curie, Paris, France, Pol. Acad. Sci., Warsaw, Poland, CEA-CNRS, Univ. J. Fourier, Grenoble, France, CNRS-Thomson, Orsay, France

9.30 a.m.

- Th-b03 Ultrafast spin dynamics in diluted magnetic semiconductor quantum wells**, R. Akimoto, K. Ando, F. Sasaki, S. Kobayashi, and T. Tani, Electrotechnical Lab., Tsukuba, Japan

9.45 a.m.

- Th-b04 Nonlinear excitonic Faraday effects in CdTe/CdMnTe quantum wells**, P. Leisching, C. Buss, J. Cibert, R. Frey, and C. Flytzanis, Ecole Polytechnique, Palaiseau, France, Univ. J. Fourier, Grenoble, France

10.00 a.m.

- Th-b05 The role of spin glass theory for semimagnetic semiconductors**, R. Oppermann, B. Rosenow, and A. Chudnovskiy, Univ. Würzburg, Würzburg, Germany

10.15 a.m.

- Th-b06 Bose-condensation of exciton magnetic polarons in semimagnetic quantum wells**, A.V. Kavokin, Univ. degli Studi Pavia, Pavia, Italy

10.30 a.m. - 11.00 a.m. Coffee Break

HETEROSTRUCTURES III

(11.00 a.m. - 12.30 p.m.)

Session A - Auditorium ATRIA Centre

11.00 a.m. (invited)

- Th-a06 Thermalization of free excitons in ZnSe quantum wells**, H. Kalt, M. Umlauff, J. Hoffmann, W. Langbein, J.M. Hvam, M. Scholl, J. Söllner, M. Heuken, B. Jobst, and D. Hommel, Univ. Karlsruhe, Karlsruhe, Germany, Mikroelektronik Center, Lyngby, Denmark, Inst. für Halbleitertechnik, RWTH Aachen, Aachen, Germany, Univ. Bremen, Bremen, Germany

11.30 a.m.

- Th-a07 Optical properties of laser diodes and heterostructures based on Beryllium chalcogenides**, U. Zehnder, D.R. Yakovlev, W. Ossau, Th. Gerhard, F. Fischer, Th. Litz, H.J. Lugauer, A. Waag, and G. Landwehr, Univ. Würzburg, Würzburg, Germany

11.45 a.m.

- Th-a08 High resolution X-ray diffraction and X-ray reflectivity studies of short period CdTe/MnTe superlattices**, J. Stangl, M. de Naurois, A.A. Darhuber, S. Ferreira, W. Faschinger, and G. Bauer, J. Kepler Univ. Linz, Linz, Austria

12.00 a.m.

- Th-a09 Interface roughness correlation in CdTe/CdZnTe strained quantum wells**, N.T. Pelekanos, N. Boudet, J. Eymery, and H. Mariette, CEA-CNRS, Univ. J. Fourier, Grenoble, France

12.15 a.m.

- Th-a10 Measurements of the critical thickness of ZnSe and ZnCdSe grown on GaAs by X-ray topography**, C. O'Donnell, G. Lacey, G. Horsburgh, A.G. Cullis, C.R. Whitehouse, P.J. Parbrook, W. Meredith, G.D. Brownlie, B. Vögele, I. Galbraith, K.A. Prior, and B.C. Cavenett, Heriot-Watt Univ., Edinburgh, UK, Univ. Sheffield, Sheffield, UK

DOPING II

(11.00 a.m. - 12.30 p.m.)

Session B - Amphitheatre ESC

11.00 a.m.

- Th-b07 Nitrogen dopant site within the ZnSe lattice as studied by ion beam analysis**, H. Kobayashi, K. Kimura, F. Nishiyama, S. Miwa, and T. Yao, Sony Corp. Res. Center, Yokohama, Japan, JRCAT, Tsukuba, Japan, Hiroshima Univ., Hiroshima, Japan, Tohoku Univ., Sendai, Japan

11.15 a.m.

- Th-b08 Configuration of dopant atoms in ZnSe and ZnTe**, K. Akimoto, T. Kobayashi, T. Ogawa, W. Ohtuka, T. Maruyama, and Y. Kitajima, Univ. Tsukuba, Tsukuba, Japan, Nat. Lab. for High Energy Phys., Tsukuba, Japan

11.30 a.m.

- Th-b09 Neutralisation of nitrogen acceptors in MBE-grown ZnTe by intentional incorporation of hydrogen**, H. Pelletier, B. Theys, J. Chevallier, and N. Magnea, CNRS, Meudon, France, CEA-Grenoble, Grenoble, France

11.45 a.m.

- Th-b10 Beta-NMR on implanted boron and nitrogen in ZnSe**, B. Itermann, E. Diehl, M. Füllgrabe, M. Heemeier, F. Kroll, F. Mai, P. Meier, K. Marbach, D. Peters, H. Thiess, G. Welker, H. Ackermann, H.-J. Stöckmann, W.-D. Zeitz, H. Wenisch, and D. Hommel, Univ. Marburg, Marburg, Germany, Hahn-Meitner Inst., Bereich FD, Berlin, Germany, Univ. Bremen, Germany

12.00 a.m.

- Th-b11 DLTS and drift mobility measurements on MBE-grown nitrogen doped ZnSe**, I.S. Hauksson, D. Seghier, H.P. Gislason, G.D. Brownlie, K.A. Prior, and B.C. Cavenett, Univ. of Iceland, Reykjavik, Iceland, Heriot-Watt Univ., Edinburgh, U.K.

12.15 a.m.

- Th-b12 Energy transfer processes and photoluminescence properties of homogeneously and delta-doped ZnS:Mn**, W. Park, T. Jones, S. Schön, W. Tong, B.K. Wagner, and C.J. Summers, Georgia Inst. Tech., Atlanta, USA

12.30 p.m. - 2.00 p.m. Lunch

MICROCAVITIES

(2.00 p.m. - 3.45 p.m.)

Session A - Auditorium ATRIA Centre

2.00 p.m. (invited)

- Th-a11 Strong coupling in microcavities: theory and applications**, Vincenzo Savona, Ecole Polytech. Féd. Lausanne, Lausanne, Switzerland

2.30 p.m.

- Th-a12 Quantum microcavities in II-VI semiconductors: strong coupling regime in vertical cavity lasers**, P. Kelkar, A.V. Nurmikko, C.-C. Chu, J. Han, W.-L. Chen, and R.L. Gunshor, Brown Univ., Providence, USA, Purdue Univ., West Lafayette, USA

2.45 p.m.

- Th-a13 Coherent exciton-polariton dynamics in high quality II-VI semiconductor microcavities**, F. Quochi, G.R. Hayes, R. André, J.L. Staehli, and Le Si Dang, Ecole Polytech. Féd. Lausanne, Lausanne, Switzerland, Univ. J. Fourier, Grenoble, France

3.00 p.m.

- Th-a14 MBE growth of monolithic MgZnSSe/ZnSSe/CdZnSe microcavity LED structures**, P. Uusimaa, A. Rinta-Möykky, S. Orsila, A. Salokatve, and M. Pessa, Tampere Univ. Tech., Tampere, Finland

3.15 p.m.

- Th-a15 Optical properties of polaritons built from large oscillator strength QW excitons in Cd(Mn,Mg)Te microcavities**, R. André, J. Bleuse, D. Heger, F. Kany, Le Si Dang, Y. Merle d'Aubigné, and H. Ulmer, CEA-CNRS, Univ. J. Fourier, Grenoble, France

3.30 p.m.

- Th-a16 Exciton Bragg reflectors: theory and experiment**, E.L. Ivchenko, A.F. Ioffe Phys.-Tech. Inst., St. Petersburg, Russia, Univ. Würzburg, Würzburg, Germany

NARROW GAP SEMICONDUCTORS

(2.00 p.m. - 3.45 p.m.)

Session B - Amphitheatre ESC

2.00 p.m.

- Th-b13 The segregation phenomena in CMT melts and structural features in cadmium and mercury tellurides in a liquid phase**, Vasilii M. Glazov, and Lidiya M. Pavlova, Moscow Inst. Electron. Eng., Univ., Moscow, Russia

2.15 p.m.

- Th-b14 Heteroepitaxy of CdTe on (211)Ge substrates by molecular beam epitaxy**, J.P. Zanatta, P. Ferret, P. Duvaut, G. Thérét, G. Rolland, and A. Million, LETI / CEA-Grenoble, France

2.30 p.m.

- Th-b15 Arsenic doping in HgCdTe grown by MBE**, P.S. Wijewarnasuriya, and S. Sivananthan, Univ. of Illinois, Chicago, USA

2.45 p.m.

- Th-b16 Growth and optical properties of (112)B HgTe/HgCdTe superlattices**, C.R. Becker, A. Pfeuffer-Jeschke, V. Latussek, K. Ortner, M. Li, W. Tang, and G. Landwehr, Univ. Würzburg, Würzburg, Germany, Chinese Acad. Sci., Shanghai, China

3.00 p.m.

- Th-b17 Density dependent electron cyclotron resonance in an inverted CdTe/HgTe/CdTe quantum well**, M. Schultz, U. Merkt, A. Sonntag, U. Rossler, T. Colin, P. Helgesen, T. Skauli, and S. Lovold, Univ. Hamburg, Hamburg, Germany, Univ. Regensburg, Regensburg, Germany, Norwegian Defense Res. Establishment, Kjeller, Norway

3.15 p.m.

Th-b18 Magnetic field and dimensionality induced population effects in HgSe:Fe/HgSe heterostructures and superlattices, O. Portugall, N. Puhlmann, H.U. Müller, M. Barczewski, I. Stolpe, G. Machel, M. von Ortenberg, D. Schikora, T. Widmer, and H. Lischka, Humboldt Univ. Berlin, Berlin, Germany, Univ. Paderborn, Paderborn, Germany

3.30 p.m.

Th-b19 Giant magnetoresistance in Hg(1-x)Cd(x)Te and applications for high density magnetic recording, T. Thio, S.A. Solin, J.W. Bennet, D.R. Hines, M. Kawano, N. Oda, and M. Sano, NEC Research Institute, Princeton, USA, Imperial College, London, United Kingdom, NEC Corporation, Kanagawa, Japan

3.45 p.m. - 6.00 p.m. POSTER SESSION II

FRIDAY**SURFACES AND INTERFACES***(9.00 a.m. - 10.30 a.m.)*

9.00 a.m. (invited)

- Fr-01 Characterization and control of II-VI / III-V heterovalent interfaces**, Akihiro Ohtake, Shiro Miwa, Li-Hsin Kuo, Tetsuji Yasuda, Kozo Kimura, Chengguo Jin, and Takafumi Yao, JRCAT, Tsukuba, Japan

9.30 a.m.

- Fr-02 Assignment of RDS peaks to surface layers**, M.R. Schmid, K. Hingerl, D. Stifter, A. Bonanni, and H. Sitter, Profactor GmbH, Steyr, Austria, Univ. Linz, Linz, Austria

9.45 a.m.

- Fr-03 A scanning tunneling microscopy study of the growth of cadmium telluride: the role of the c(2x2) and (2x1) reconstructions**, D. Martrou, P. Gentile, and N. Magnea, CEA-Grenoble, France

10.00 a.m.

- Fr-04 Local interface composition and band discontinuities in molecular-beam epitaxially grown BeTe/ZnSe heterostructures**, M. Nagelstrasser, H. Dröge, F. Fischer, T. Litz, A. Waag, G. Landwehr, and H.-P. Steinrück, Univ. Würzburg, Würzburg, Germany

10.15 a.m.

- Fr-05 Interfacial properties of ZnSe/GaAs heterovalent interfaces**, F. Lu, K. Kimura, S.Q. Wang, Z.Q. Zhu, and T. Yao, Tohoku Univ., Sendai, Japan, Joint Res. Center Atom Tech., Tsukuba, Japan

*10.30 a.m. - 11.00 a.m. - Coffee Break***NANOSTRUCTURES***(11.00 a.m. - 12.30 p.m.)*

11.00 a.m. (invited)

- Fr-06 Excitons in nanocrystals**, P. Lavallard, Univ. Paris 6 et 7, France

11.30 a.m.

- Fr-07 Excitons and biexcitons trapped on self-organised CdTe islands in wide ZnTe quantum wells**, T. Taliercio, P. Lefebvre, N. Magnea, J. Allègre, and H. Mathieu, Univ. Montpellier II, Montpellier, France, CEA-Grenoble, Grenoble, France

11.45 a.m.

- Fr-08 Disorder-induced exciton localization in a fractional-monolayer ZnSe/CdSe superlattice**, A.A. Toropov, S.V. Ivanov, T.V. Shubina, A.V. Lebedev, S.V. Sorokin, P.S. Kop'ev, G.R. Pozina, J.P. Bergman, and B. Monemar, A.F. Ioffe Phys. Technical Inst., St Petersburg, Russia, Univ. Linköping, Linköping, Sweden

12.00 a.m.

- Fr-09 Exciton localization in CdSe islands buried into a quantum well of ZnCdSe, F. Gindele, U. Woggon, W. Langbein, J. Hvam, K. Leonardi, K. Ohkawa, and D. Hommel, Univ. Karlsruhe, Karlsruhe, Germany, Univ. Denmark, Lyngby, Denmark, Univ. Bremen, Bremen, Germany**

12.15 a.m.

- Fr-10 Hot exciton relaxation in CdZnSe/ZnSe quantum wells and quantum dots, G. Bacher, R. Spiegel, T. Kümmell, A. Forchel, B. Jobst, D. Hommel, and G. Landwehr, Univ. Würzburg, Würzburg, Germany**

12.30 p.m. *Closing Session*

II-VI '97

SCIENTIFIC PROGRAMME SCHEDULE

Poster Sessions

TUESDAY POSTER SESSION*(3.30 p.m. - 6.00 p.m.)***Section A: Bulk and Epitaxial Growth, Surfaces**

- Tu-P01 Growth and characterization of novel MgSe/ZnCdSe quasi-quaternaries on InP substrates**, Hiroyuki Shinbo, Wataru Shinozaki, Takeshi Nagano, Ichirou Nomura, Akihiko Kikuchi, and Katsumi Kishino, Sophia Univ., Tokyo, Japan
- Tu-P02 CdSe/ZnSe strained layer superlattices grown on InP**, Y. Nabetani, H. Takahashi, T. Kato, and T. Matsumoto, Faculty of Eng., Yamanashi Univ., Kofu, Japan
- Tu-P03 Interplay of kinetics and thermodynamics in molecular beam epitaxy of (Mg,Zn,Cd)/(S,Se)**, S. Ivanov, S. Sorokin, I. Krestnikov, N. Faleev, B. Ber, I. Sedova, and P. Kop'ev, A.F. Ioffe Phys.-Tech. Inst., St. Petersburg, Russia
- Tu-P04 Deposition and growth with desorption for CdTe molecular beam epitaxy**, Alberto Pimpinelli, Philippe Peyla, Joël Cibert, and Serge Tatarenko, ILL, Grenoble, France, LPM2C et Lab. Spectro. Phys., Univ. J. Fourier, Grenoble, France
- Tu-P05 Modelling MBE growth of II-VI semiconductors by ab initio calculations**, S. Gundel, W. Spahn, T. Gerhard, A. Waag, W. Faschinger, and G. Landwehr, Univ. Würzburg, Würzburg, Germany
- Tu-P06 Quantitative growth investigation of zincblende ZnMgSe/GaAs(100) and ZnSe/GaAs(100) by means of RHEED, HRXRD and thickness monitoring**, T. Frey, T. Reisinger, B. Folger, M. Kastner, and W. Gebhardt, Univ. Regensburg, Regensburg, Germany
- Tu-P07 Hetero-epitaxial growth of Zn(Mg)BeSe wide band-gap alloys on GaAs substrates**, V. Bousquet, E. Tournié, M. Lätigt, P. Vennéguès, and J.-P. Faurie, CRHEA-CNRS, Sophia Antipolis, Valbonne, France
- Tu-P08 Optimized metalorganic vapour phase epitaxy of ZnMgSSe heterostructures**, H. Kalisch, M. Lünenbürger, H. Hamadeh, J. Xu, M. Heuken, RWTH Aachen, Aachen, Germany
- Tu-P09 Growth mode behaviour of ZnSe epilayers on (100) GaAs at early stages of MOVPE nucleation**, N. Lovergine, G. Leo, S. Oktik, M. Catalano, A.M. Mancini, and L. Vasanelli, Univ. di Lecce, Lecce, Italy, Istituto IME-CNR, Lecce, Italy
- Tu-P10 Structural characterization of MOVPE grown ZnMgSSe/ZnSe heterostructures by HRXRD**, J. Xu, M. Lünenbürger, H. Kalisch, H. Hamadeh, J. Woitok, M. Heuken, RWTH Aachen, Germany
- Tu-P11 Studies on structural and electro-optical properties of MOVPE grown ZnMgSSe by CL and STEM**, Q. Liu, G. Brockt, A. Meinert, H. Kalisch, M. Heuken, and H. Lakner, G. Mercator Univ. Duisburg, Duisburg, Germany, RWTH Aachen, Aachen, Germany
- Tu-P12 TEM-investigation of the critical thickness anisotropy of MBE-grown ZnSe/GaAs and ZnMgSe/GaAs**, H. Preis, T. Frey, T. Reisinger, and W. Gebhardt, Univ. Regensburg, Regensburg, Germany
- Tu-P13 Structural investigations of polytypes in ZnMgSe by transmission electron microscopy and X-ray diffraction**, U. Falke, F. Firszt, A. Cichos-Bruska, H. Meczynska, P. Dluzewski, W. Paszkowicz, and M. Hietschold, Tech. Univ. Chemnitz, Chemnitz, Germany, Kopernikus Univ., Torun, Poland, Pol. Acad. Sci., Warsaw, Poland

- Tu-P14 The role of surface defects on CdTe (100): new information from high resolution low energy electron diffraction**, M. Sokolowski, H. Neureiter, M. Schneider, S. Tatarenko, C. Heske, R. Fink, and E. Umbach, Univ. Würzburg, Germany, CNRS, Univ. J. Fourier, Grenoble, France
- Tu-P15 Band offset transitivity in II-VI / III-V heterojunctions**, E. Milocco, S. Rubini, L. Sorba, and A. Franciosi, TASC-INFN, Trieste, Italy
- Tu-P16 Surface structural transformation of CdTe induced by lateral parameter relaxation: an in-situ surface X-ray diffraction study**, V.H. Etgens, M. Sauvage-Simkin, S. Tatarenko, J. Alvarez, and S. Ferrer, Univ. Curie, Paris, France, LURE, Orsay, France, CNRS, Univ. J. Fourier, Grenoble, France, ESRF, Grenoble, France
- Tu-P17 REELS measurements on CdTe (100) and ZnSe (100) surfaces**, H. Dröge, M. Nagelstrasser, A. Fleszar, J. Nürnberger, W. Faschinger, and H.-P. Steinrück, Univ. Würzburg, Würzburg, Germany
- Tu-P18 Ambient cross-sectional STM/S characterization of ZnSe/buffer/GaAs interfaces**, A.V. Ankudinov, S.I. Ivanov, A.N. Titkov, and A. Waag, A.F. Ioffe Phys.-Tech. Inst., St Petersburg, Russia, Univ. Würzburg, Würzburg, Germany
- Tu-P19 ZnSe heteroepitaxy on GaAs (001) and GaAs(110)**, S. Miwa, K. Kimura, L.H. Kuo, T. Yasuda, A. Ohtake, C.G. Gin, and T. Yao, JRCAT-ATP, Tsukuba, Japan, JRCAT-NAIR, Tsukuba, Japan, Tsukuba Univ., Tsukuba, Japan, Tohoku Univ., Sendai, Japan
- Tu-P20 A Raman study of coupled plasmon-LO phonon modes at ZnSe/GaAs interfaces**, O. Pagès, M. Soltani, A. Zaoui, M. Certier, T. Cloître, R.L. Aulombard, D. Bormann, and B. Khelifa, Univ. Metz, Metz, France, GES-CNRS, Univ. Sci. Tech. Languedoc, Montpellier, France, Univ. Artois, Lens, France
- Tu-P21 Magneto-optic study of II-VI semiconductors with treated surfaces**, S. Yu. Verbin, and B.V. Novikov, St Petersburg Univ., St Peterhof, Russia
- Tu-P22 Contribution to the understanding of the CdTe surface chemistry**, A. Etcheberry, F. Iranzo-Marin, R. Triboulet, and C. Debiemme-Chouvy, Univ. Versailles, Versailles, France, CNRS, Bellevue, Meudon, France
- Tu-P23 New results on the solid phase recrystallization of ZnSe**, S. Fusil, P. Lemasson, J.O. Nday, A. Rivière, B. Qu'hen, A. Lussan, G. Neu, E. Tournié, G. Geoffroy, A. Zozime, and R. Triboulet, CNRS, Bellevue, Meudon, France, CRHEA-CNRS, Sophia Antipolis, Valbonne, France, LSI, Ecole Polytech., Palaiseau, France
- Tu-P24 ZnO crystal growth by sublimation and chemical vapor transport (SCVT)**, J.M. Ntep, M. Barbé, D. Cohen-Solal, A. Lussan, and R. Triboulet, CNRS, Bellevue, Meudon, France
- Tu-P25 CdTe and CdZnTe crystals grown by physical vapor transport: morphology and its dependence on the growth conditions**, W. Palosz, K. Graszka, D. Gillies, M.A. George, E.E. Collins, K.T. Chen, Y. Zhang, Z. Hu, A. Burger, H. Chung, B. Raghoeamachar, and M. Dudley, USRA/NASA, Huntsville, USA, IP PAS, Warsaw, Poland, NASA-MSFC, Huntsville, USA, Fisk Univ., Nashville, USA, SUNY, New York, USA
- Tu-P26 Improvements in production of CdZnTe crystals grown by the Bridgman method**, H.L. Glass, A.J. Socha, C.L. Parfeniuk, and D.W. Bakken, Johnson Matthey Electronics, Spokane, Washington, USA
- Tu-P27 Low defect density, substrate quality crystals of the large gap II-VI compounds, obtained by physical vapour transport technique (PVT)**, A. Mycielski, E. Lusakowska, A. Szadkowski, and L. Kowalczyk, Pol. Acad. Sci., Warsaw, Poland
- Tu-P28 High-quality conducting zinc selenide substrates for molecular beam epitaxy**, U. Rinas, M. Prokesch, and H. Hartmann, Inst. für Kristallzüchtung im Forschungsverbund Berlin, Berlin, Germany

- Tu-P29** **Solution growth of zinc selenide bulk crystals**, A.-D. Weber, M. Müller, A. Winnacker, and D. Hofmann, Univ. Erlangen-Nürnberg, Erlangen, Germany
- Tu-P30** **Growth and characterisation of CdMgSe mixed crystals**, F. Firszt, S. Legowski, H. Meszynska, J. Szatkowski, and W. Paszkowicz, N. Copernicus Univ., Torun, Poland, Polish Acad. Sci., Warsaw, Poland

Section B: Materials Characterization (Doping, Defects)

- Tu-P31** **Optical orientation of excitons in CdSSe under resonant excitation in magnetic field**, A. Kiselev, A. Kornievsky, S. Permogorov, A. Reznitsky, S. Verbin, H. Gerlach, M. Hetterich, M. Grün, and C. Klingshirn, A.F. Ioffe Phys.-Tech. Inst., St Petersburg, Russia, Univ. Karlsruhe, Karlsruhe, Germany
- Tu-P32** **Optical band gap of Zn(x)Mg(1-x)S thin films with composition x between 0.14 and 1.0**, Ryou Inoue, Masahiko Kitagawa, Takayoshi Nishigaki, Kunio Ichino, Hiroshi Kobayashi, Masakazu Ohishi, and Hiroshi Saito, Tottori Univ., Tottori, Japan, Okayama Univ. Sci., Okayama, Japan
- Tu-P33** **Effect of disorder on exciton dynamics in cation-substituted ZnCdS mixed crystals**, S. Shevel, V. Vozny, M. Vytrykhivsky, A. Euteneuer, R. Hellmann, E.O. Göbel, W. Petri, and C. Klingshirn, Inst. Phys., Inst. Semicon. Phys., Kyiv, Ukraine, Philipps Univ. Marburg, Marburg, Germany, Univ. Karlsruhe, Karlsruhe, Germany, Phys.-Tech. Bundesanstalt, Braunschweig, Germany
- Tu-P34** **Structural and optical properties of ZnMgSe alloys grown on GaAs substrates by molecular beam epitaxy**, D. Huang, Y. Wei, X. Wang, D. Wang, C. Jin, J. Wang, and X. Wang, Fudan Univ., Shanghai, China
- Tu-P35** **Disorder effects on electronic and optical properties in ZnSeTe**, A. Zaoui, M. Certier, M. Ferhat, and O. Pagès, Univ. Metz, L.S.O.M., Metz, France
- Tu-P36** **Temperature dependence of excitonic luminescence from high-quality ZnS epitaxial layers**, S. Nakamura, T. Sakashita, Y. Yamada, and T. Taguchi, Yamaguchi Univ., Yamaguchi, Japan
- Tu-P37** **Optical absorption in CdTe, CdZnTe and CdS at elevated temperatures**, J.T. Mullins, R.C. Aylemore, D.M. Huntley, A.W. Brinkman, Univ. Durham, Durham, UK
- Tu-P38** **p-type contacts based on beryllium-chalcogenides**, H.-J. Lugauer, T. Baron, C. Behr, F. Fischer, Th. Litz, K. Schüll, A. Waag, and G. Landwehr, Univ. Würzburg, Würzburg, Germany
- Tu-P39** **Palladium thin film contacts on p-type ZnSe: adjustment of electrical properties by reaction diffusion**, Rainer Schmid-Petzer, Tech. Univ. Clausthal, Clausthal-Zellerfeld, Germany
- Tu-P40** **Schottky barrier tunability in Al/ZnSe interfaces**, M. Lazzarino, G. Bratina, G. Scarel, S. Rubini, L. Sorba, and A. Franciosi, TASC-INFM, Trieste, Italy
- Tu-P41** **Shallow compensating donors in nitrogen-doped ZnSe epitaxial layers**, E. Tournié, C. Morhain, G. Neu, and J.-P. Faurie, CRHEA-CNRS, Sophia Antipolis, Valbonne, France
- Tu-P42** **Heavily doped p-type ZnSe formation by an excimer laser doping**, Y. Hatanaka, T. Arakawa, D. Noda, T. Aoki, and Y. Nakanishi, Shizuoka Univ., Hamamatsu, Japan
- Tu-P43** **Mechanism for photo-assisted nitrogen doping of ZnSe**, M.U. Ahmed, P. Prete, S.J.C. Irvine, A. Stafford, L.M. Smith, A.C. Jones, and S.A. Rushworth, NEWI, Wrexham, UK, Epichem Ltd., Merseyside, UK
- Tu-P44** **Electron beam activation of acceptors in MOVPE ZnSe:N**, V.I. Kozlovsky, A.B. Krysa, W. Taudt, and M. Heuken, Lebedev Phys. Inst. of RAS, Moscow, Russia, Inst. für Halbleitertechnik, Aachen, Germany

- Tu-P45 Time-resolved photoluminescence of ZnSe:N: further studies**, I. Kuskovsky and G.F. Neumark, Columbia Univ., New York, USA
- Tu-P46 Analysis of time-resolved DAP spectra of ZnSe:Li and ZnSe:N**, P. Bäume, S. Strauf, J. Gutowski, M. Behringer, and D. Hommel, Univ. Bremen, Bremen, Germany
- Tu-P47 Electrical transport and trap properties in nitrogen doped p-type MBE grown ZnSe layers on GaAs using different contact materials**, G. Prösch, R. Beyer, M. Behringer, M. Fehrer, H. Burnghardt, E. Thomas, D. Hommel, and D.R.T. Zahn, Tech. Univ. Chemnitz, Chemnitz, Germany, Univ. Bremen, Bremen, Germany
- Tu-P48 Nitrogen doping of Te based II-VI heterostructures**, A. Arnoult, S. Tatarenko, D. Ferrand, J. Cibert, A. Hauray, A. Wasieleski, and Y. Merle d'Aubigné, CEA-CNRS, Univ. J. Fourier, Grenoble, France
- Tu-P49 PD-defect-complexes in ZnTe and CdTe and interaction with group-V-elements**, S. Hermann, H.-E. Mahnke, B. Spellmeyer, M. Wienecke, B. Reinhold, R.A. Yankov, and H.-E. Gumlich, Hahn-Meitner-Inst. Berlin GmbH, Berlin, Germany, Humboldt Univ. Berlin, Germany, Forschungszentrum Rossendorf, Dresden, Germany, Tech. Univ. Berlin, Germany
- Tu-P50 Photoelectrical and deep level characterization of vanadium-doped CdTe and CdZnTe**, Kh. Allachen, M. Tapiero, Z. Guellil, J.P. Zielinger, and J.C. Launay, Inst. Phys. Chem. Mat. Strasbourg, Strasbourg, France, Inst. Chem. Mat. Cond. Bordeaux, Pessac, France
- Tu-P51 Bandgap level of the Cd vacancy in CdTe**, U. Reislöhner, J. Grillenberger, and W. Witthuhn, Univ. Jena, Jena, Germany
- Tu-P52 Point defect concentration calculations in CdTe**, P. Fochouk, O. Korovyanko, and O. Panchouk, Univ. of Chernivtsi, Chernivtsi, Ukraine
- Tu-P53 Vacancy-type defects in highly resistive and conducting CdTe role in the compensation**, C. Corbel, H. Kauppinen, L. Liskay, L. Baroux, K. Saarinen, P. Hautojärvi, R. Triboulet, Y. Marfaing, P. Gilet, and A. Basset, INSTN, CEA-Saclay, Gif sur Yvette, France, Helsinki Univ. Tech., Espoo, Finland, CNRS, Bellevue, Meudon, France, LETI / CEA-Grenoble, Grenoble, France
- Tu-P54 A comparative study on deep levels in P-ZnSe grown by MBE, MOMBE and MOVPE**, M. Funato, Sz. Fujita, and Sg. Fujita, Kyoto Univ., Kyoto, Japan
- Tu-P55 Deep levels in ZnSe epitaxial layers examined by piezoelectric photoacoustic spectroscopy**, Kenji Yoshino, Atsuhiko Fukuyama, Kouji Maeda, Minoru Yoneta, Hiroshi Saito, Masakazu Ohishi, and Tetsuo Ikari, Miyazaki Univ., Miyazaki, Japan, Okayama Univ., Okayama, Japan
- Tu-P56 Characterization of reactive ion etching induced type conversion in p-type HgCdTe using scanning laser microscopy**, J.F. Siliquini, J.M. Dell, C.A. Musca, and L. Faraone, Univ. Western Australia, Nedlands, Australia
- Tu-P57 Non-uniformity of Hg diffusion in p-type HgCdTe**, H. Ebe, T. Okamoto, and K. Yamoto, Fujitsu Lab. Ltd., Atsugi, Japan
- Tu-P58 Achievement of p-type low carrier concentration for MOCVD grown HgCdTe without annealing process**, K. Matsushita, K. Shigenaka, and A. Kamata, Toshiba Corp., Kawasaki, Japan
- Tu-P59 Iodine and Arsenic doping of (100) HgCdTe/GaAs grown by metalorganic vapor phase epitaxy using isopropyl iodine and tris-dimethylarminoarsenic**, Jong-Hyeon Song, Je-Won Kim, Man-Jang Park, Jin-Sang Kim, Kwan-Uk Jung, and Sang-Hee Suh, Korea Univ., Seoul, South Korea, Korea Inst. Sci. and Tech., Seoul, South Korea
- Tu-P60 Spectroscopy of interface states in HgTe/HgCdTe superlattices**, M.von Truchsess, A. Pfeuffer-Jeschke, V. Latussek, C.R. Becker, and E. Batke, Univ. Würzburg, Würzburg, Germany

- Tu-P61 Comparative study of passivation processes of HgCdTe by oxydation in basic media**, Frank Lefèvre, Dominique Lorans, C. Debiemme-Chouvy, Dominique Ballutaud, and Robert Triboulet, SAGEM SA, St Benoît, France, IREM, Univ. Versailles, Versailles, France, CNRS, Bellevue, Meudon, France
- Tu-P62 Crystallinity improvement of HgCdTe films grown by liquid phase epitaxy technique**, Biao Li, Junhao Chu, Jiqian Zhu, and Dingyuan Tang, Nat. Lab. for IR Phys., Shanghai Inst. Tech. Phys., Shanghai, China

Section C: Properties of Low Dimensional Systems

- Tu-P63 Magneto-optical properties of the excitons in fractional-monolayer ZnTe structures and ZnTe islands self-organized effects**, Q.X. Zhao, N. Magnea, and M. Willander, Chalmers Univ. Technol. and Göteborg Univ., Göteborg, Sweden, CEA-Grenoble, France
- Tu-P64 Well width dependence of electron and hole g-factors in CdTe/CdMgTe structures**, Q.X. Zhao, N. Magnea, M. Oestreich, and M. Willander, Chalmers Univ. Technol. and Göteborg Univ., Göteborg, Sweden, CEA-Grenoble, France, MPI Stuttgart, Germany
- Tu-P65 Homogeneous linewidth of direct exciton in a type-II ZnSe/BeTe quantum wells**, A.V. Platonov, D.R. Yakovlev, U. Zehnder, W. Ossau, V. Kochereshko, F. Fischer, Th. Litz, A. Waag, and G. Landwehr, Univ. Würzburg, Würzburg, Germany, A.F. Ioffe Phys.-Techn. Inst., St. Petersburg, Russia
- Tu-P66 Optical and acoustical phonon properties of BeTe**, V. Wagner, S. Gundel, J. Geurts, R. Kruse, Ch. Becker, U. Küster, T. Gerhard, Th. Litz, H.-J. Lugauer, F. Fischer, A. Waag, and G. Landwehr, Univ. Würzburg, Würzburg, Germany, RWTH Aachen, Aachen, Germany
- Tu-P67 Relative oscillator strengths of neutral and negatively charged excitons in CdTe quantum wells**, R.B. Miller, T. Baron, R.T. Cox, and K. Saminadayar, La Trobe Univ. Bundoora, Australia, CEA-Grenoble, Univ. J. Fourier, Grenoble, France
- Tu-P68 Bound and unbound exciton-electron states in II-VI quantum well structures with 2DEG**, V. Kochereshko, D.R. Yakovlev, W. Ossau, A. Waag, G. Landwehr, P.M.C. Christianen, J.C. Maan, T. Wojtowicz, M. Kutrowski, G. Karczewski, and J. Kossut, A.F. Ioffe Phys.-Techn. Inst., St. Petersburg, Russia, Univ. Würzburg, Würzburg, Germany, Univ. of Nijmegen, Nijmegen, The Netherlands, Pol. Acad. Sci, Warsaw, Poland
- Tu-P69 Exciton-electron interactions in CdTe/CdMgTe modulation-doped QW structures**, V. Kochereshko, D.R. Yakovlev, W. Ossau, G. Landwehr, T. Wojtowicz, M. Kutrowski, G. Karczewski, and J. Kossut, A.F. Ioffe Phys.-Techn. Inst., Russian Acad. of Sci., St. Petersburg, Russia, Univ. Würzburg, Würzburg, Germany, Polish Acad. of Sci., Warsaw, Poland
- Tu-P70 Fermi-edge singularity in the luminescence spectra of II-VI modulation doped quantum wells**, G. Coli, L. Calcagnile, P.V. Giugno, R. Rinaldi, A. Franciosi, L. Vanzetti, L. Sorba, and R. Cingolani, INFN, Univ. Lecce, Italy, TASC, Trieste, Italy
- Tu-P71 Interband transition studies on CdZnTe/ZnTe step quantum wells under applied electric fields**, H.L. Park and T.W. Kim, Yonsei Univ., Seoul, Korea, Kwangwoon Univ., Seoul, South Korea
- Tu-P72 Band-offset determination of the ZnCdSe/ZnSe interface**, C. Guénaud, E. Deleporte, A. Filoramo, Ph. Lelong, C. Delalande, C. Morhain, E. Tournié, J.P. Faurie, ENS, Paris, France, CRHEA/CNRS, Sophia Antipolis, Valbonne, France
- Tu-P73 Ultrathin CdSe quantum wells**, K.G. Chinyama, I.V. Bradley, C. Trager-Cowan, K.P. O'Donnell, P.I. Kuznetsov, A.P. Chernushich, and V. Luzanov, Univ. Strathclyde, Glasgow, UK, IRE, Russian Acad. Sci., Moscow, Russia

- Tu-P74** **Exciton and carrier tunneling processes and high density effect in ZnCdSe/ZnSe asymmetric double quantum wells**, J.N. Zeng, M.C. Debnath, I. Souma, Y. Amemiya, and Y. Oka, Tohoku Univ., Sendai, Japan, CREST, JST, Saitama, Japan
- Tu-P75** **Investigations of the composition variations of quaternary MgZnSSe-epilayers by high resolution x-ray diffraction**, T. Gerhard, M. Behringer, W. Faschinger, and G. Landwehr, Univ. Würzburg, Würzburg, Germany, Univ. Bremen, Bremen, Germany
- Tu-P76** **Excitation, relaxation and recombination of excitons in MQW ZnCdSe/ZnSe structures**, S. Permogorov, A. Reznitsky, L. Tenishev, A. Kornievsky, S. Verbin, S. Ivanov, S. Sorokin, W. von der Osten, H. Stolz, and M. Jütte, A.F. Ioffe Phys.-Tech. Inst., St Petersburg, Russia, Univ. Paderborn, Paderborn, Germany
- Tu-P77** **New Approach to the fabrication of CdSe/ZnSe quantum dots using cleaved edge overgrowth**, Hyun-Chul Ko, Yoichi Kawakami, Shizuo Fujita, and Shigeo Fujita, Kyoto Univ., Kyoto, Japan
- Tu-P78** **Influence of inhomogeneous strain relaxation on the photoluminescence of II-VI wire-structures**, Y.M. Niquet, C. Gourgon, Le Si Dang, H. Mariette, C. Priester, C. Vieu, H. Straub, G. Brunthaler, A. Darhuber, Th. Grill, W. Faschinger, and G. Bauer, Univ. J. Fourier, Grenoble, France, Inst. Electr. Microélectr. Nord, Villeneuve d'Asq, France, CNRS, Bagneux, France, Univ. Linz, Linz, Austria
- Tu-P79** **Micro-cathodoluminescence study of ZnSe quantum dots embedded in ZnS fabricated by molecular beam epitaxy**, K. Arai, Z. Zhu, T. Sekiguchi, T. Yasuda, F. Lu, Y. Segawa, N. Kuroda, and T. Yao, Tohoku Univ., Sendai, Japan, Photodyn. Res. Center, Inst. Phys. Chem. Res. (RIKEN), Sendai, Japan, Joint Res. Center Atom Tech., Tsukuba, Japan
- Tu-P80** **Magneto-photoluminescence studies of ZnMnTe/ZnTe multiple quantum well and quantum dot structures**, I.J. Griffin, P.J. Klar, D. Wolferson, J.J. Davies, B. Lunn, D.E. Ashenford, and T. Henning, Univ. East Anglia, Norwich, UK, Univ. Hull, Hull, UK, Univ. Göteborg and Calmers Univ. Tech., Göteborg, Sweden
- Tu-P81** **CdS nanocrystal growth in thin silica films: evolution of size distribution function**, M. Gandais, S. Gurevich, A. Ekimov, I. Kudryavtsev, O. Lublinskaya, and A. Osinskii, CNRS, Univ. Paris VI and VII, Paris, France, A.F. Ioffe Inst. Tech. Inst., St Petersburg, Russia
- Tu-P82** **Resonant low-frequency Raman scattering in CdS-doped glasses**, L. Saviot, B. Champagnon, E. Duval, and A.I. Ekimov, LPCML-CNRS, Univ. Lyon I, Villeurbanne, France, A.F. Ioffe Phys.-Tech. Inst., St-Petersburg, Russia
- Tu-P83** **Electroluminescence in thin solid films of closely-packed CdS nanocrystals**, M.V. Artemyev, V. Sperling, and U. Woggon, Belarussian State Univ., Minsk, Belarus, Univ. Karlsruhe, Germany
- Tu-P84** **Formation of II-VI nanocrystals in a novel phosphate glass**, A.A. Lipovskii, E.V. Kolobkova, and V.D. Petrikov, St. Petersburg State Tech. Univ., St. Petersburg, Russia, A.F. Ioffe Phys.-Tech. Inst., St. Petersburg, Russia
- Tu-P85** **Three dimensionally diluted magnetic semiconductors clusters in range of sizes and compositions: spectroscopic properties depending on the synthesis mode**, L. Levy, N. Feltin, D. Ingert, and M.P. Pileni, Univ. Paris VI, France, CEA-Saclay, Gif sur Yvette, France
- Tu-P86** **EPR and ENDOR investigations on CdS:Mn nanocrystals**, D.M. Hofmann, G. Counio, A. Hofstaetter, U. Leib, and B.K. Meyer, Justus-Liebig Univ., Giessen, Germany, CNRS-Ecole Polytechnique, Palaiseau, France
- Tu-P87** **Electron-hole long-range exchange interaction in semiconductor quantum dots**, S.V. Goupalov and E.L. Ivchenko, A.F. Ioffe Phys.-Tech. Inst., St. Petersburg, Russia

- Tu-P88 Zeeman splitting of excitons in CdTe/CdMnTe quantum wells**, A.K. Bhattacharjee and G. Fishman, Univ. Paris Sud, Orsay, France, Univ. J. Fourier, Grenoble, France
- Tu-P89 Inter-quantum well exciton transfer in CdTe/CdMnTe MQW structures**, M. Godlewski, M. Surma, Z. Wilamowski, T. Wojtowicz, G. Karczewski, J. Kossut, P.O. Holtz, J.P. Bergman, and B. Monemar, Polish Acad. Sci., Warsaw, Poland, Linköping Univ., Linköping, Sweden
- Tu-P90 Magnetoluminescence study of CdTe/CdMnTe MQW structures**, Yu. G. Kusrayev, B.P. Zakharchenya, G. Karczewski, T. Wojtowicz, and J. Kossut, A.F. Ioffe Phys.-Tech. Inst., St. Petersburg, Russia, Polish Acad. of Sci., Warsaw, Poland
- Tu-P91 Magneto-optical anisotropy of semimagnetic ADQW structures**, W. Heimbrod, M. Happ, D. Suisky, F. Neugebauer, B. Lunn, and D.E. Ashenford, Humboldt Univ. zu Berlin, Berlin, Germany, Univ. Hull, Hull, UK
- Tu-P92 Interdiffusion in annealed CdMnTe/CdTe/CdMgTe quantum wells studied by Zeeman effect**, S. Mackowski, Nguyen The Khoi, P. Kossacki, A. Golnik, J.A. Gaj, A. Lemaitre, C. Testelin, C. Rigaux, G. Karczewski, T. Wojtowicz, and J. Kossut, Warsaw Univ., Warsaw, Poland, Univ. Paris 6 and 7, Paris, France, Polish Acad. of Sci., Warsaw, Poland
- Tu-P93 Magneto-optical study of interface broadening of CdTe/CdMnTe quantum wells**, S. Kuroda, K. Kojima, K. Takita, K. Uchida, and N. Miura, Univ. Tsukuba, Tsukuba, Japan, Univ. Tokyo, Tokyo, Japan
- Tu-P94 II-VI piezoelectric-barrier heterostructures for infrared light modulation**, Valentin Ortiz, Nikos T. Pelekanos and Guido Mula, CEA-Grenoble, Grenoble, France
- Tu-P95 Space-charge effects in type-II strained layer superlattices**, J. Creasey, I.V. Bradley, and K.P. O'Donnell, Univ. Strathclyde, Glasgow, UK
- Tu-P96 CdS-ZnSe intrinsic Stark superlattices**, I.V. Bradley, J. Creasey, K.P. O'Donnell, B. Neubauer, and D. Gerhsen, Univ. Strathclyde, Glasgow, UK, Univ. Karlsruhe, Germany
- Tu-P97 Screened excitons in wide-gap semiconductors and quantum wells**, Mikhail Portnoi and Ian Galbraith, Heriot-Watt Univ., Edinburgh, UK
- Tu-P98 Coherent phenomena and interaction of excitons in wide ZnSe-ZnMgSe single quantum wells**, H.P. Wagner, A. Schätz, R. Maier, T. Reisinger, W. Gebhardt, W. Langbein, and J.M. Hvam, Univ. Regensburg, Regensburg, Germany, Mikroelec. Center, The Tech. Univ. Denmark, Lyngby, Denmark
- Tu-P99 Four-wave mixing in CdMnTeSe:In crystals**, B. Koziarska-Glinka, M. Ponder, T. Wojtowicz, I. Miotkowski, and A. Suchocki, Polish Acad. Sci., Warsaw, Poland, Purdue Univ., West Lafayette, Indiana, USA

Section D: Optoelectronic Devices

- Tu-P100 Beryllium substitution-mediated covalency engineering of II-VI alloys for lattice elastic rigidity reinforcement**, C. Verie, CNRS, Sophia Antipolis, Valbonne, France
- Tu-P101 Lateral and longitudinal mode control in CdZnSe-based laser diodes**, D. Eisert, M. Legge, G. Bacher, A. Forchel, J. Nünberger, K. Schüll, W. Faschinger, and G. Landwehr, Univ. Würzburg, Würzburg, Germany
- Tu-P102 New device concepts for II-VI photonics using Be-VI compounds**, F. Fischer, G. Reuscher, Th. Litz, H.J. Lugauer, M. Keim, Th. Baron, A. Waag, and G. Landwehr, Univ. Würzburg, Würzburg, Germany
- Tu-P103 Optical gain in ZnCdSe-ZnSe quantum wells**, F.P. Logue, P. Rees, J.F. Heffernan, C. Jordan, J.F. Donegan, J. Hegarty, F. Hiei, S. Taniguchi, T. Hino, K. Nakano, and A. Ishibashi, Trinity College, Dublin, Ireland, Sony Res. Centre, Yokohama, Japan

- Tu-P104 Degradation dynamics in ZnCdSe laser diodes**, C. Jordan, D.T. Fewer, S.J. Hewlett, J.F. Donegan, F.P. Logue, E.M. McCabe, J. Hegarty, S. Taniguchi, T. Hino, K. Nakano, and A. Ishibashi, Trinity College, Dublin, Ireland, Sony Res. Centre, Yokohama, Japan
- Tu-P105 Saturation of optical gain in ZnSe heterostructures**, H. Kalt, M. Umlauff, M. Kraushaar, M. Scholl, J. Söllner, and M. Heuken, Univ. Karlsruhe, Karlsruhe, Germany, RWTH Aachen, Aachen, Germany
- Tu-P106 Lasing and dynamics of photoexcited carriers in graded index separate confinement ZnCdSe single quantum well lasers**, L. Calcagnile, M. Lomascolo, R. Cingolani, L. Sorba, L. Vanzetti, and A. Franciosi, INFN, Univ. Lecce, Lecce, Italy, TASC-INFN, Trieste, Italy
- Tu-P107 Gain to absorption conversion by increasing excitation density in excitonic waveguides**, V. Kutzer, M. Strassburg, A. Hoffmann, I. Broser, N.N. Ledentsov, U.W. Pohl, D. Bimberg, S.V. Ivanov, and I.L. Krestnikov, TU-Berlin, Berlin, Germany, A.F. Ioffe Phys.-Tech. Inst., St. Petersburg, Russia
- Tu-P108 Spectro-temporal gain dynamics of optically pumped II-VI multiple-quantum-well structures**, K. Wundke, U. Neukirch, P. Michler, J. Gutowski, M. Behringer, and D. Hommel, Univ. Bremen, Bremen, Germany
- Tu-P109 Lasing and optical properties of MOVPE ZnSe/ZnMgSSe QW heterostructures at high optical excitation**, G.P. Yablonskii, A.L. Gurskii, I.P. Marko, V.N. Yuvchenko, H. Hamadeh, H. Kalisch, and M. Heuken, Belarus Acad. Sci., Minsk, Belarus, RWTH Aachen, Aachen, Germany
- Tu-P110 Optical gain enhancement at the photonic band edge of a 3D photonic crystal**, Yu.A. Vlasov, K. Luterova, I. Pelant, B. Hönerlage, V. N. Astratov, and A.A. Kaplyanskii, IPCMS-GONLO, Strasbourg, France, A.F. Ioffe-PTI, St. Petersburg, Russia, AVCR, Prague, Czech Republic

THURSDAY POSTER SESSION

(3.45 p.m. - 6.00 p.m.)

Section A: Bulk and Epitaxial Growth, Surfaces

- Th-P01 Selective area growth of ZnSe and ZnS by MOMBE**, A. Ueta, M. Arita, A. Avramescu, K. Uesugi, T. Numai, I. Suemune, H. Machida, and N. Shimoyama, Hokkaido Univ., Sapporo, Japan, Trichemical Lab., Japan
- Th-P02 Rapid thermal metalorganic chemical vapor deposition of II-VI compounds**, S. Stolyarova, N. Amir, and Y. Nemirovsky, Technion, Haifa, Israel
- Th-P03 Growth of ZnSe on misoriented GaAs (110) surface by MBE**, K.W. Koh, M.H. Cho, Z. Zhu, T. Hanada, M. Isshiki, and T. Yao, Tohoku Univ., Sendai, Japan, Tohoku Univ., Sendai, Japan
- Th-P04 Growth of ZnSe on (211) GaAs substrates**, S.A. Telfer, G. Horsburgh, J.S. Milnes, P.J. Thompson, K.A. Prior, and B.C. Cavenett, Heriot-Watt Univ., Edinburgh, UK, NEC Semic. (UK) Ltd., Livingston West Lothian, UK
- Th-P05 Molecular beam epitaxy of wurtzite CdSe on GaAs (111) substrates**, Masakazu Ohishi, Hiroshi Saito, Minoru Yoneta, Hironobu Sawada, and Souta Mori, Okayama, Univ. Sci., Okayama, Japan
- Th-P06 Growth of ZnSe based multilayer devices using elemental sulphur source**, G.D. Brownlie, W. Meredith, J.S. Milnes, K.A. Prior, and B.C. Cavenett, Heriot-Watt Univ., Edinburgh, UK
- Th-P07 Structural and optical properties of ZnS_{0.5}Te_{0.5}/ZnTe-superlattices on (001) GaAs-substrates grown by molecular-beam-epitaxy**, M. Korn, D. Albert, A. Gerhard, W. Faschinger, and G. Landwehr, Univ. Würzburg, Würzburg, Germany
- Th-P08 MOVPE growth of ZnS_{0.5}Se_{0.5}/GaAs (100) using ditertiarybutylselenium, tertiary-butyl-sulfide and dimethylzinc triethylamine precursors**, C. Thiandoume, O. Ka, C. Cohen, A. Bouanani, A. Lusson, M. Rommeluère, A. Tromson-Carli, and O. Gorochov, CNRS, Bellevue, Meudon, France, Fac. Sci., Dakar, Sénégal
- Th-P09 Fine structure of free exciton luminescence spectra in heteroepitaxial ZnSe/GaAs**, A.L. Gurskii, Yu. P. Rakovich, W. Taudt, A.A. Gladyschuk, G.P. Yablonskii, and M. Heuken, Belarus Acad. Sci., Minsk, Belarus, Brest Polytech. Inst., Brest, Belarus, Inst. für Halbleitertechnik, RWTH Aachen, Aachen, Germany
- Th-P10 Temperature dependent measurements on ZnSe heterostructures with high resolution X-ray diffractometry**, V. Grossmann, H. Heinke, M. Behringer, and D. Hommel, Univ. Bremen, Bremen, Germany
- Th-P11 Start of misfit relaxation in GaAs-ZnSe heterostructures**, H.R. Ress, W. Spahn, R. Ebel, J. Nürnberger, H. Schäfer, M. Korn, W. Faschinger, and G. Landwehr, Univ. Würzburg, Würzburg, Germany
- Th-P12 Pulsed laser annealing of CdTe epilayers and superlattices**, D. Sands, S. Chalk, J.H.C. Hogg, J.E. Nicholls, M.O'Neill, B. Lunn, and D.E. Ashenford, Univ. Hull, Hull, UK
- Th-P13 CdTe/MnTe superlattices studied by X-ray experiments**, J. Eymery, J.M. Hartmann, and J.L. Rouvière, CEA-Grenoble, France
- Th-P14 CdHgTe electrodeposition thin films and their properties**, M. Dergacheva, V. Statsyuk, L. Fogel, Inst. Org. Catalysis and Electrochem., Almaty, Kazakhstan

- Th-P15 Study on minority carrier lifetime of HgZnTe by photoconductive decay method,** K.H. Kim, K.N. Oh, J.K. Hong, Y.C. Chung, S.U. Kim, and M.J. Park, Korea Univ., Seoul, South Korea
- Th-P16 Lattice dynamics of HgSe and beta-HgS,** W. Szuszkiewicz, K. Dybko, E. Dynowska, J. Gorecka, B. Witkowska, B. Hennion, M. Jouanne, and C. Julien, Polish Acad. Sci., Warsaw, Poland, Lab. Léon Brillouin, CEA-Saclay, France, Lab. Milieux Hétérogènes et Désordonnés, Paris, France
- Th-P17 The computer calculation of homogeneity area of Zn, Cd, and Hg tellurides and alloy between them,** V.M. Glazov, L.M. Pavlova, and A.S. Pashinkin, Moscow Inst. Electron. Eng., Moscow, Russia
- Th-P18 Peculiarities of solid-liquid phase transition in CdTe,** L. Shcherbak, Chernivtsi State Univ., Chernivtsi, Ukraine
- Th-P19 Vapour phase and liquid phase doping of zinc selenide by III group elements,** A.N. Georgobiani, A.S. Nasibov, P.V. Shapkin, and U.A. Aminov, Lebedev Phys. Inst., Moscow, Russia
- Th-P20 Homo-epitaxial growth of ZnSe by vapor phase epitaxy and characterization of the grown layers,** S. Kishimoto, T. Ogasawara, T. Hasegawa, T. Fukuda, and S. Iida, Nagaoka Univ. Tech., Nagaoka, Japan, Tohoku Univ., Sendai, Japan
- Th-P21 Non-destructive, room temperature quality control of CdTe,** Igor Lyubomirsky, M.K. Rabinal, Vera Lyahovitskaya, and David Cahen, Weizmann Inst. Sci., Rehovot, Israel

Section B: Materials Characterization (Doping, Defects)

- Th-P22 Hydrogen-related photoluminescence in CdTe,** J. Hamann, D. Blass, A. Burchard, C. Casimir, M. Deicher, T. Filz, R. Magerle, V. Ostheimer, C. Schmitz, H. Wolf, and Th. Wichert, Univ. Saarlandes, Saarbrücken, Germany, Fakultät Phys., Univ. Konstanz, Germany
- Th-P23 Chlorine related "hot" photoluminescence in CdTe,** P.N. Tkachuk, V.I. Tkachuk, N.D. Korbutjak, A.N. Raransky, D.V. Korbutyak, and S.G. Krylyuk, Chernivtsi State Univ., Chernivtsi, Ukraine, National Acad. of Sci. of Ukraine, Kiev, Ukraine
- Th-P24 Optical spectra and electronic structure of CdFeTe mixed crystals,** T.P. Surkova, S.A. Permogorov, L.N. Tenishev, and V.R. Galakhov, Russian Acad. Sci., Ekaterinburg, Russia, A.F. Ioffe Phys.-Tech. Inst. Russian Acad. Sci., St-Petersburg, Russia
- Th-P25 EXAFS analysis of bond lengths in selected ZnS-based diluted magnetic semiconductors,** R.J. Iwanowski, K. Lawniczak-Jablonska, Z. Golacki, and A. Traverse, Polish Acad. Sci., Warsaw, Poland, LURE, Univ. Paris-Sud, Orsay, France
- Th-P26 Characterisation of CdO thin films deposited by activated reactive evaporation,** K.T. Ramakrishna, and C. Sravani, Univ. Northumbria, Newcastle, UK, Indian Inst. Sci., Bangalore, India
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TRAVEL INFORMATION

There are many ways to reach Grenoble:

By Air:

Scheduled national and international flights arrive at the international airports of Lyon - Satolas (France, 80 km from Grenoble) and Geneva - Cointrin (Switzerland, 150 km from Grenoble). Shuttle buses (from Lyon) and trains (from Geneva) connect the two airports to Grenoble railway station. Fare is about 150 FF in both cases. National flights arrive at the Grenoble - St. Geoirs airport (40 km from Grenoble), connected to Grenoble by shuttle buses.

By Rail:

The Grenoble railway station is well served by trains arriving from Paris (3hrs) and Lyon (1hr). The high speed TGV trains require advance booking. From Geneva, there are fewer direct connections and you may have to change your train at Chambéry station.

By Road:

There are two toll motorways arriving in Grenoble, the A41 (from Geneva) and the A48 (from Lyon). If you reach Grenoble by the A48 motorway from Lyon, at ~3 km from Grenoble follow the sign "Grenoble Bastille", and if you reach Grenoble by the A41 motorway from Geneva follow the sign "Grenoble centre". Entering Grenoble you will find directions to reach the railway station (*Gare SNCF*), where a large underground toll parking station is available.

The Atria conference centre is behind the station and 2 min. walk from the bus terminal (*Gare Routière*) and railway station. It is reached by a pedestrian passage under the railway tracks.

Please check if a visa is required to enter France from your country.

TRAIN AND BUS TIMETABLE

Only direct connections are listed

Valid for Sunday 24 August 1997

GENEVA - GRENOBLE		
departure time	arrival time	train number
6:54	9:00	5684
9:30	11:41	5680
15:32	17:45	5612
18:38	20:50	5616
22:22	00:41	5692

Valid for Saturday 23 and Sunday 24 August 1997

PARIS - GRENOBLE		
departure time	arrival time	train number
9:48	12:55	TGV 607
14:34	17:41	TGV 907
19:48	22:51	TGV 913

Buses on Saturday 23 August 1997

LYON AIRPORT - GRENOBLE	
departure time	arrival time
8:30	9:35
9:30	10:35
11:00	12:05
12:15	13:20
14:15	15:20
16:30	17:35
18:30	19:35
19:30	20:35
21:45	23:10

Buses on Sunday 24 August 1997

LYON AIRPORT - GRENOBLE	
departure time	arrival time
8:30	9:35
11:00	12:05
12:15	13:20
14:15	15:20
15:15	16:20
16:30	17:35
17:30	18:35
19:30	20:35
21:30	22:35
22:45	00:10

N.B. If you arrive at the Grenoble St. Geoires Airport, there is a bus connection with each plane.

USEFUL ADDRESSES

Office du Tourisme (Grenoble Tourist Information Centre) : 14, rue de la République, Tel. +33-(0)476 424 141

Lyon - Satolas Airport : Tel. + 33 - (0)478 719 221

Lyon Airport Limousine : Tel. + 33 - (0)474 048 022

Geneva - Cointrin Airport : Tel. + 41 - 157 15 00

Grenoble St. Geoirs Airport : Tel. + 33 - (0)476 654 848

Grenoble Railway Station (Gare SNCF) : 1, pl. de la Gare, Tel. + 33 - (0)476 475 050

Grenoble Bus Station (Gare Routière): Tel. +33 - (0)476 879 031

Grenoble Radio Taxis : 14, rue de la République, Tel. + 33 - (0)476 544 254

II-VI'97 Conference (Registration Desk at the Atria Centre) : Tel. (0)476 708 445

USEFUL PRACTICAL INFORMATION

Telephone calls

Nearly all French telephone booths need a telephone card that you can buy in post offices and in many newspapers shops. Most phone booths accept credit cards (VISA and MASTERCARD / EUROCARD). Please note that inside France telephone numbers are now 10 digit numbers which at present all begin with a zero. From anywhere within France *always* dial the zero (e.g. to call the conference Registration Desk from France you have to dial 0476 708 445), from outside France drop the zero. For calling another country from France, dial 00 before dialling the international code of the country. If you want to make an international telephone call by operator dial 0033 followed by the international code of the desired country.

Banks

A number of different banks can be found in the area around the city centre (Place Grenette, see the Grenoble centre map for details). Usual opening time of exchange desks are from 9:00 a.m. to 11:30 a.m. and from 1:30 p.m. to 4:00 p.m. from Monday to Friday.

CONFERENCE EXHIBITORS

ADDON

AIXTRON

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JOHNSON MATTHEY

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PHILIPS

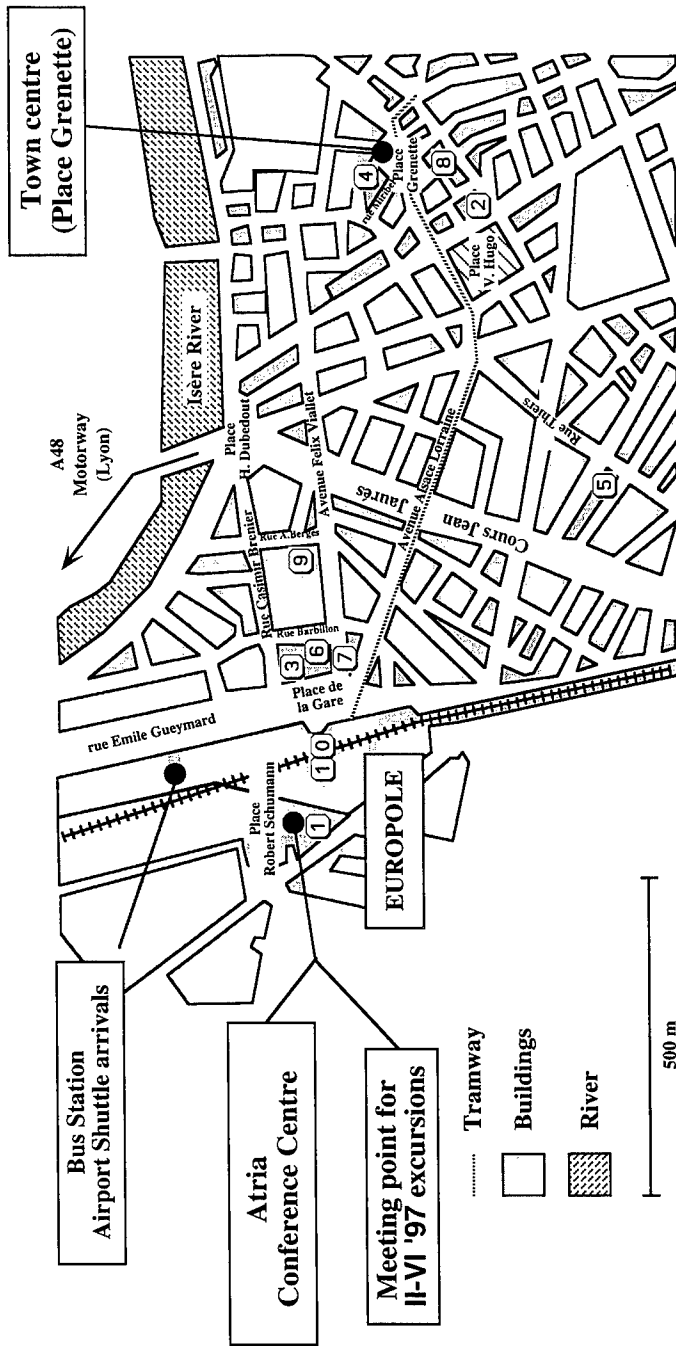
RHONE ALPES MERCURE

RIBER

SCANTEK

SOFRADIR

GRENOBLE CENTRE MAP



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|-------------------------------|-------------------------------|
| ① Novotel Atria *** | ⑨ Hotel Gloria ** |
| ② Hotel d'Angleterre *** | ⑩ RAILWAY STATION (Gare SNCF) |
| ③ Hotel Terminus *** | |
| ④ Hotel Ibis ** | |
| | |
| ⑤ Hotel Splendid ** | |
| ⑥ Hotel de l'Institut ** | |
| ⑦ Hotel Suisse et Bordeaux ** | |
| ⑧ Hotel de l'Europe ** | |

	MONDAY	TUESDAY	WEDNESDAY	THURSDAY	FRIDAY
8:30 - 8:45					
8:45 - 9:00	Opening Session		Diluted Magnetic Semiconductors I		
9:00 - 10:00	Lasers I	Lasers II		Materials (ATRIA Auditorium)	Surfaces and Interfaces
10:00 - 10:30			COFFEE BREAK	Diluted Magnetic Semiconductors II (ESC Amphitheatre)	
10:30 - 11:00	COFFEE BREAK			COFFEE BREAK	
11:00 - 12:00	Doping I	Non Linear Optics	Heterostructures II	Heterostructures III (ATRIA Auditorium)	Nanostructures II
12:00 - 12:30					
12:30 - 12:45			LUNCH		Closing Session
12:45 - 14:00	LUNCH			LUNCH	LUNCH
14:00 - 15:30	Heterostructures I	Detectors	EXCURSION	Microcavities (ATRIA Auditorium)	Visit of European Synchrotron Radiation Facility
15:30 - 16:00	COFFEE BREAK			Narrow Gap Semiconductors (ESC Amphitheatre)	
16:00 - 17:30	Nanostructures I	Posters I	Departure time: 13:15	Posters II (including post-deadline papers)	
17:30 - 18:00					
	City Reception 19:00	Special Session Wide Bandgap Lasers 20:00		Banquet Departure time: 18:30	